

	Hits	Search Text	DBs
34	0	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) same (wet near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4 or polymer\$4 or slurr\$4)) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((conductive or structure or pedestal) near29 gate))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
35	1	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) same (wet near9 etch\$4) same (remov\$4 or strip\$4 or wash\$4 or eliminat\$4) same (residu\$4 or polymer\$4 or slurr\$4)) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near29 (conductive or metal\$3 or gate))))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
36	84	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near29 (conductive or metal\$3 or gate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
37	50	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near22 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and ((first near22 (liner or SiN or SiON)) same (substrate or wafer)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near29 (conductive or gate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
38	2	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same (conductive near29 (structure or pedestal)) same (first near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PPGPUB
39	4	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same (conductive near29 (structure or pedestal)) same (first near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PPGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
40	0	430/311.ccls. and ((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near38 (conductive or metal\$3 or gate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
41	2	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and (second near26 (liner or SiON or SiN)) and (liner same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same (conductive near29 (structure or pedestal)) same (first near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PGPUB

	Hits	Search Text	DBs
42	0	430/312.ccls. and ((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near38 (conductive or metal\$3 or gate)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
43	7	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and (first near22 (liner or SiN or SiON)) and (second near26 (liner or SiON or SiN)) and (liner same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same liner) and (((conductive or gate) near29 (structure or pedestal)) same ((first or second or third) near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PGPUB

	Hits	Search Text	DBs
44	3	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and (second near26 (liner or SiON or SiN)) and (liner same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same liner) and (((conductive or gate) near29 (structure or pedestal)) same ((first or second or third) near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US - PGPUB
45	0	430/316.ccls. and ((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and ((second near26 (liner or SiON or SiN)) same ((structure or pedestal) near38 (conductive or metal\$3 or gate)))	US - PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
46	3	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and (second near26 (liner or SiON or SiN)) and (liner same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same liner) and (((conductive or gate) near29 (structure or pedestal)) same (first near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PGPUB
47	3	((substrate or wafer) same (gate near16 (conductive or structure or second or pluralit\$4 or multiple))) and (source near28 drain) and ((photoresist or resist) near26 (expos\$4 or irradiat\$4 or illuminat\$4)) and (first near22 (liner or SiN or SiON)) and (second near26 (liner or SiON or SiN)) and (liner same ((structure or pedestal) near38 (conductive or metal\$3 or gate))) and ((inter\$5layer\$5dielectric or ILD) same liner) and ((conductive near29 (structure or pedestal)) same (first near16 conductive near19 (layer or deposit\$4 or coat\$4 or film)))	US-PGPUB